

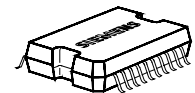
Smart Quad Channel Low-Side Switch

Features

- Shorted Circuit Protection
- Overtemperature Protection
- Overvoltage Protection
- Parallel Control of the Inputs (PWM Applications)
- Separate Diagnostic Pin for Each Channel
- Power - SO 20 - Package with integrated cooling area
- Standby mode with low current consumption
- μ C compatible Input
- Electrostatic Discharge (ESD) Protection

Product Summary

Supply voltage	V_S	4.8 - 32 V
Drain source voltage	$V_{DS(AZ)max}$	60 V
On resistance($T_J = 25^\circ\text{C}$)	$R_{ON(typ) 1,2}$	0.2 Ω
	$R_{ON(typ) 3,4}$	0.35 Ω
Output current	$I_{D 1,2}$	2 x 5 A
	$I_{D 3,4}$	2 x 3 A



P-DSO-20-10

Ordering Code:
Q -A

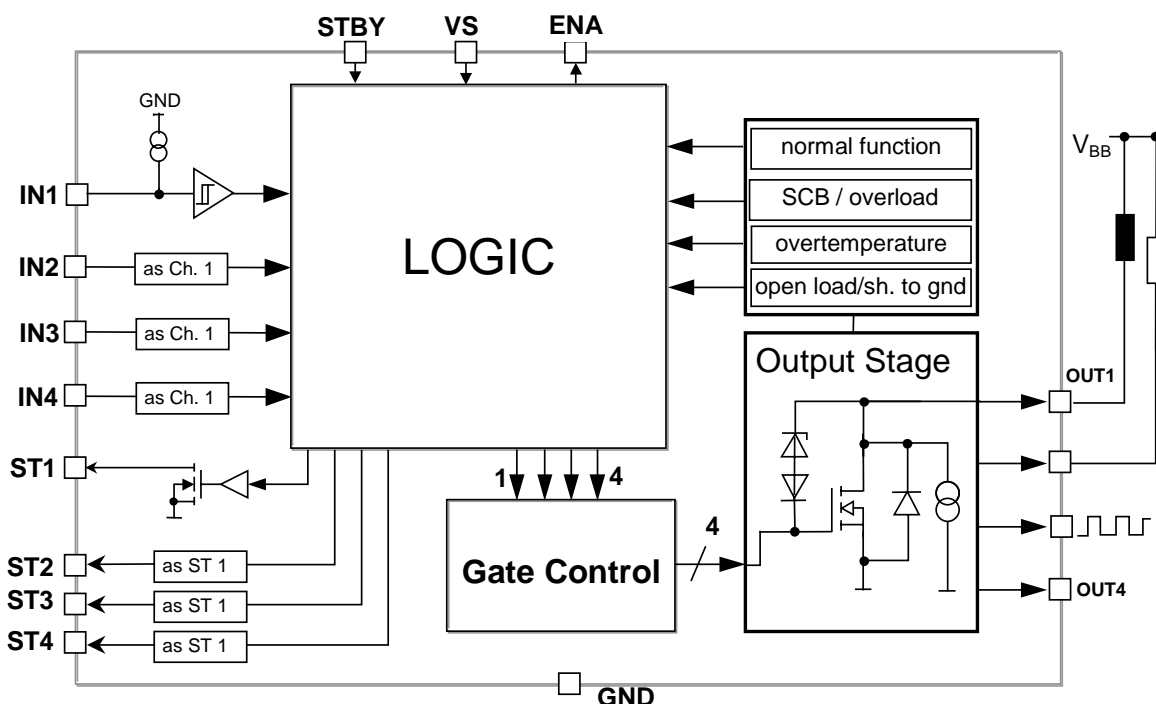
Application

- All kinds of resistive and inductive loads (relays,electromagnetic valves)
- μ C compatible power switch for 12 and 24 V applications
- Solenoid control switch in automotive and industrial control systems
- Robotic Controls

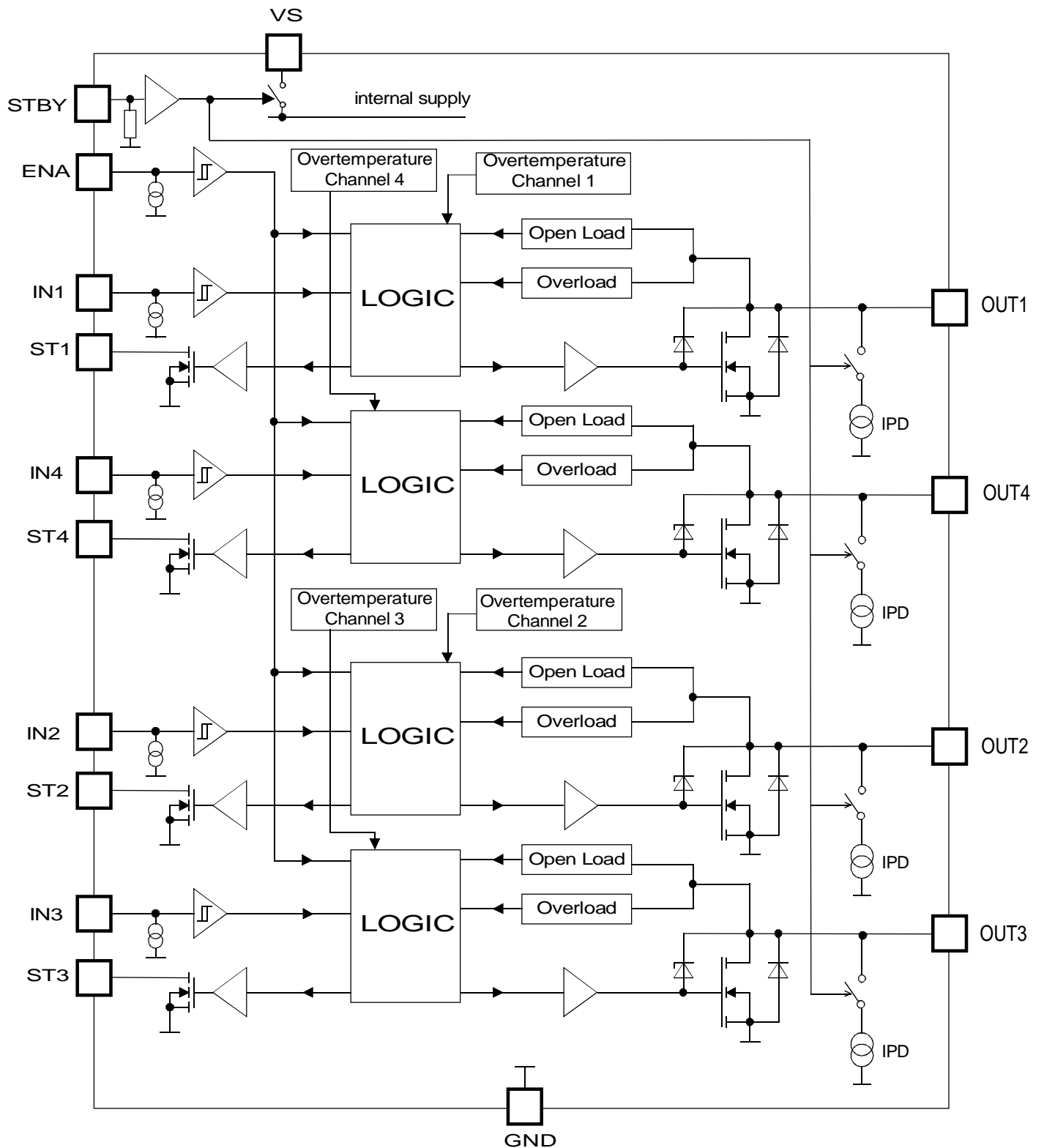
General description

Quad channel Low-Side-Switch (2x5A/2x3A) in Smart Power Technology (SPT) with four separate inputs and four open drain DMOS output stages. The TLE 6228 GP is fully protected by embedded protection functions and designed for automotive and industrial applications. Each channel has its own status signal for diagnostic feedback. Therefore the TLE 6228 GP is particularly suitable for ABS or Powertrain Systems.

Block Diagram



Detailed Block Diagram



Pin Description

Pin	Symbol	Function
1	GND	Ground
2	OUT1	Power Output channel 1
3	ST1	Status Output channel 1
4	IN4	Control Input channel 4
5	VS	Supply Voltage
6	STBY	Standby
7	IN3	Control Input channel 3
8	ST2	Status Output channel 2
9	OUT2	Power Output channel 2
10	GND	Ground
11	GND	Ground
12	OUT3	Power Output channel 3
13	ST3	Status Output channel 3
14	IN2	Control Input channel 2
15	GND	Ground Logic
16	ENA	Enable Input for all four channels
17	IN1	Control Input channel 1
18	ST4	Status Output channel 4
19	OUT4	Power Output channel 4
20	GND	Ground

Pin Configuration (Top view)

GND	1 ●	20	GND
OUT1	2	19	OUT4
ST1	3	18	ST4
IN4	4	17	IN1
VS	5	16	ENA
STBY	6	15	GNDL
IN3	7	14	IN2
ST2	8	13	ST3
OUT2	9	12	OUT3
GND	10	11	GND

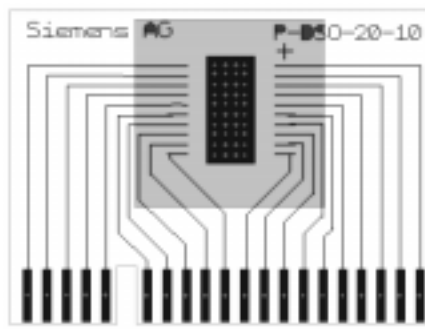
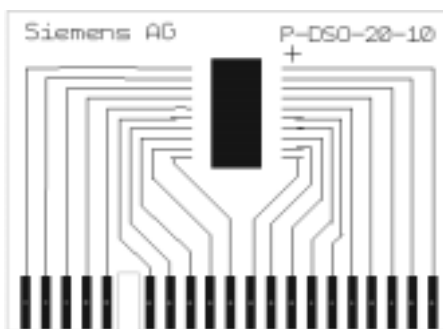
P - DSO - 20 - 10

Heat slug internally connected to ground pins

Maximum Ratings for $T_j = -40^{\circ}\text{C}$ to 150°C

The maximum ratings may not be exceeded under any circumstances, not even momentarily and individually, as permanent damage to the IC will result.

Parameter	Symbol	Values	Unit
Supply voltage	V_S	-0.3 ... + 40	V
Continuous drain source voltage (OUT1...OUT4)	V_{DS}	45	V
Input voltage IN1 to IN4, ENA	V_{IN}, V_{ENA}	- 0.3 ... + 6	V
Input voltage STBY	V_{STBY}	- 0.3 ... + 40	
Status output voltage	V_{ST}	- 0.3 ... + 32	V
Load Dump Protection $V_{Load\ Dump} = U_P + U_S$; $U_P = 13.5\text{ V}$ Load tbd $R_l^{1)} = 2\ \Omega$; $t_d = 400\text{ms}$; IN = low or high With $R_L = \text{tbd}\ \Omega$ ($I_D = 2\text{A}$) $R_l = 2\ \Omega$; $t_d = 400\text{ms}$; IN = low or high	$V_{Load\ Dump}^{2)}$	tbd tbd	V
Operating temperature range	T_j	- 40 ... + 150	$^{\circ}\text{C}$
Storage temperature range	T_{stg}	- 55 ... + 150	
Output current per channel (see page 6)	$I_{D(lim)}$	overload shutdown	A
Status output current	I_{ST}	- 5 ... + 5	mA
Inductive load switch off dissipation energy $T_j = 25^{\circ}\text{C}$	E_{AS}	50	mJ
Electrostatic Discharge Voltage (human body model) according to MIL STD 883D, method 3015.7 and EOS/ESD assn. standard S5.1 - 1993	V_{ESD}	2000	V
DIN Humidity Category, DIN 40 040		E	
IEC Climatic Category, DIN IEC 68-1		40/150/56	
Thermal resistance junction - case junction - ambient @ min. footprint junction - ambient @ 6 cm^2 cooling area	R_{thJC} R_{thJA}	2 50 38	K/W



Minimum footprint

PCB with heat pipes,
backside 6 cm^2 cooling area

¹⁾ R_l = internal resistance of the load dump test pulse generator LD200

²⁾ $V_{LoadDump}$ is setup without DUT connected to the generator per ISO 7637-1 and DIN 40 839.

Electrical Characteristics

Parameter and Conditions $V_S = 4.8$ to 18 V ; $T_j = -40$ °C to $+150$ °C (unless otherwise specified)	Symbol	Values			Unit
		min	typ	max	

1. Power Supply (V_S)

Supply current (Outputs ON)	I_S			8	mA
Supply current (Outputs OFF) $V_{ENA} = L$, $V_{STBY} = H$	I_S			4	mA
Standby current $V_{STBY} = L$	I_S			10	µA
Operating voltage	V_S	4.8		32	V

2. Power Outputs

ON state resistance Channel 1,2 $I_D = 1$ A; $V_S \geq 9.5$ V	$T_j = 25$ °C $T_j = 150$ °C	$R_{DS(ON)}$		0.2 0.26 0.5	Ω
ON state resistance Channel 3,4 $I_D = 1$ A; $V_S \geq 9.5$ V	$T_j = 25$ °C $T_j = 150$ °C	$R_{DS(ON)}$		0.35 0.4 0.75	Ω
Z-Diode clamping voltage (OUT1...4) $I_D \geq 100$ mA		$V_{DS(AZ)}$	45		60 V
Pull down current $V_{STBY} = H$, $V_{IN} = L$		I_{PD}	10	20	50 µA
Output leakage current $V_{STBY} = L$, $0V \leq V_{DS} \leq 35V$ $V_{STBY} = L$, $35V \leq V_{DS} \leq 45V$		I_{Dlk}			5 µA 1 mA
Output turn on time ³ $I_D = 1$ A		t_{on}	3	15	50 µs
Output turn off time ³ $I_D = 1$ A		t_{off}	3	20	60
Output on fall time ³ $I_D = 1$ A		t_{fall}	3	10	30
Output off rise time ³ $I_D = 1$ A		t_{rise}	3	10	30
Overload switch-off delay time ³		t_{DSO}	tbd	60	tbd
Output off status delay time ³		t_D	500	1200	3000
Failure extension Time for Status Report		$t_{D-failure}$	500	1200	3000
Input Suppression Time		t_{D-IN}	500	1200	3000
Output on status delay time ⁴		t_{dST}	10	50	100

3. Digital Inputs (IN1, IN2, IN3, IN4, ENA)

Input low voltage	V_{INL}	- 0.3		1.0	V
Input high voltage	V_{INH}	2.0		6.0	V
Input voltage hysteresis ⁴	V_{INHys}	50	100		mV
Input pull down current $V_{IN} = 5$ V; $V_S \geq 6.5$ V	I_{IN}	10	30	60	µA
Enable pull down current $V_{ENA} = 5$ V; $V_S \geq 6.5$ V	I_{ENA}	10	20	40	µA

4. Digital Status Outputs (ST1 - ST4) Open Drain

Output voltage low $I_{ST} = 2$ mA	V_{STL}			0.5	V
Leakage current high	I_{STH}			2	µA

³ See timing diagram, resistive load condition; $V_S \geq 9$ V

⁴ This parameter will not be tested but assured by design

Electrical Characteristics

Parameter and Conditions $V_S = 4.8$ to 18 V ; $T_j = -40$ °C to $+150$ °C (unless otherwise specified)	Symbol	Values			Unit
		min	typ	max	

5. Standby Input (STBY)

Input low voltage	V_{STBY}	0		1	V
Input high voltage	V_{STBY}	3.5		V_S	V
Input current $V_{STBY} = 18$ V	I_{STBY}			300	μA

6. Diagnostic Functions

Open load detection voltage $V_{ENA} = X, V_{IN} = L$	$V_S \geq 6.5$ V	$V_{DS(OL)}$	$0.3 \cdot V_S$	$0.33 \cdot V_S$	$0.36 \cdot V_S$	V
Open load detection current channel 1,2 $V_{ENA} = V_{IN} = H$	$V_S \geq 6.5$ V	$I_{D(OL) 1,2}$	tbd	160	tbd	mA
Open load detection current channel 3,4 $V_{ENA} = V_{IN} = H$	$V_S \geq 6.5$ V	$I_{D(OL) 3,4}$	Tbd	160	tbd	mA
Overload detection current channel 1,2	$V_S \geq 6.5$ V	$I_{D(lim) 1,2}$	5	7.5		A
Overload detection current channel 3,4	$V_S \geq 6.5$ V	$I_{D(lim) 3,4}$	3	5		A
Overtemperature shutdown threshold ⁴		T_{th}	170		200	°C
Hysteresis		T_{hys}		10		K
Pulse Width for static diagnostic output		t_{IN}			500	μs

⁴ This parameter will not be tested but assured by design

Application Description

This IC is especially designed to drive inductive loads (relays, electromagnetic valves). Integrated clamp-diodes limit the output voltage when inductive loads are discharged.

Four open-drain logic outputs indicate the status of the integrated circuit. The following conditions are monitored and signalled:

- overloading of output (also shorted load to supply) in active mode
- open and shorted load to ground in active and inactive mode
- overtemperature

Circuit Description

Input Circuits

The control and enable inputs, both active high, consist of schmitt triggers with hysteresis. All inputs are provided with pull-down current sources. Not connected inputs are interpreted as low and the respective output stages are switched off.

In standby mode (STBY = LOW) the current consumption is greatly reduced.

The circuit is active when STBY = HIGH.

If the standby function is not used, it is allowed to connect the standby pin directly to VS.

Status Signals: The status signals are undefined for 2ms after a power up event or a STBY low to high transition.

Output Stages

The four power outputs consist of DMOS-power transistors with open drains. The output stages are short circuit protected throughout the operating range. Each output has its own zenerclamp. This causes a voltage limitation at the power transistor when inductive loads are switched off.

Parallel to the DMOS transistors there are internal pull down current sources. They are provided to detect an open load condition in the off state. They will be disconnected in the standby mode.

Due to EMI measures there is an internal zenerclamp in parallel to the output stage. It gets active above 35V drain source voltage. This leads to an increasing leakage current up to 1 mA @ $V_{DS} = 40V$. See characteristics 3.5.

Protective Circuits

The outputs are protected against current overload and overtemperature. If the output current increases above the overload detection threshold I_{QO} for a longer time than t_{DSO} or the temperature increases above T_{th} , then the power transistor is immediately switched off. It remains off until the control signal at the input is switched off and on again.

Fault Detection

The status outputs indicate the switching state of the output stage. Under normal conditions is: ST = low \Rightarrow Output off; ST = high \Rightarrow Output on. If an error occurs, the logic level of the status output is inverted, as listed in the diagnostic table.

If current overload or overtemperature occurs for a longer time than t_{DSO} , the fault condition is latched into an internal register and the output is shutdown. The reset is done by switching off the corresponding control input.

Open load is detected for all four channels in on and off mode.

In the on mode the load current is monitored. If it drops below the specified threshold value I_{QU} then an open load condition is detected.

In the off mode, the output voltage is monitored. An open load condition is detected when the output voltage of a given channel is below the threshold $V_{DS(OL)}$, which is typ. 33 % of the supply voltage V_S .

Status output at pulse width operation

If the input is operated with a pulsed signal, the status does not follow each single pulse of the input signal. An internal delay t_D of typ. 1.2ms (min 500 μ s) enables a continuous status output signal. See the timing diagrams on the following pages for further information.

This internal status delay simplifies diagnostic software for pwm applications.

Diagnostic Table

In general the status follows the input signal in normal operating conditions.

If any error is detected the status is inverted.

Operating Condition	Standby Input	Enable Input	Control Input	Power Output	Status Output
	STBY	ENA	IN	Q	ST
Standby	L	X	X	off	H
Normal function	H	L	X	off	L
	H	H	L	off	L
	H	H	H	ON	H
Open load or short to ground	H	L	L	off	H
	H	L	H	off	H
	H	H	L	off	H
	H	H	H	ON	L
Overload or short to supply ¹⁾ reset latch ²⁾	H	H	H	off	L
	H	H	H \rightarrow L	off	L
	H	L	X	off	L
Overtemperature ¹⁾ reset latch ²⁾	H	H	H	off	L
	H	H	H \rightarrow L	off	L
	H	L	X	off	L

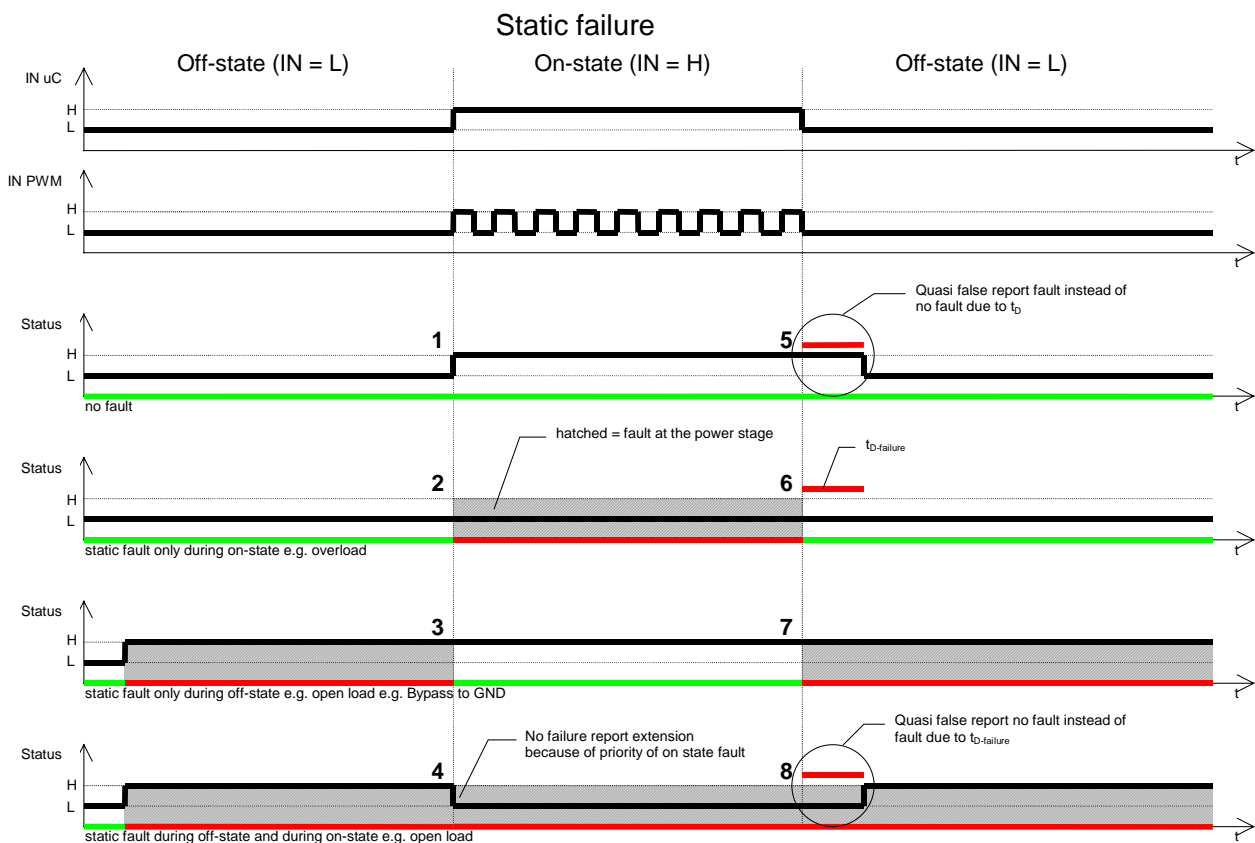
Note 1) : overload/short-to-supply/overtemperature - events shorter than min. time t_{DSO} specified in 3.10 will not be latched and not reported at the status pin.

Note 2) : to reset latched status-output in case of overload/short-to-supply/overtemperature the control input has to go low and stay low for longer than max. input suppression time t_{D-IN} specified in 3.13 of the characteristics

Failure Situations and Status Report

1. Static failure

Nr.	Off-state	On-state	Nr.	On-state	Off-state
1	no fault	no fault	5	no fault	no fault
2	no fault	fault	6	fault	no fault
3	fault	no fault	7	no fault	fault
4	fault	fault	8	fault	fault



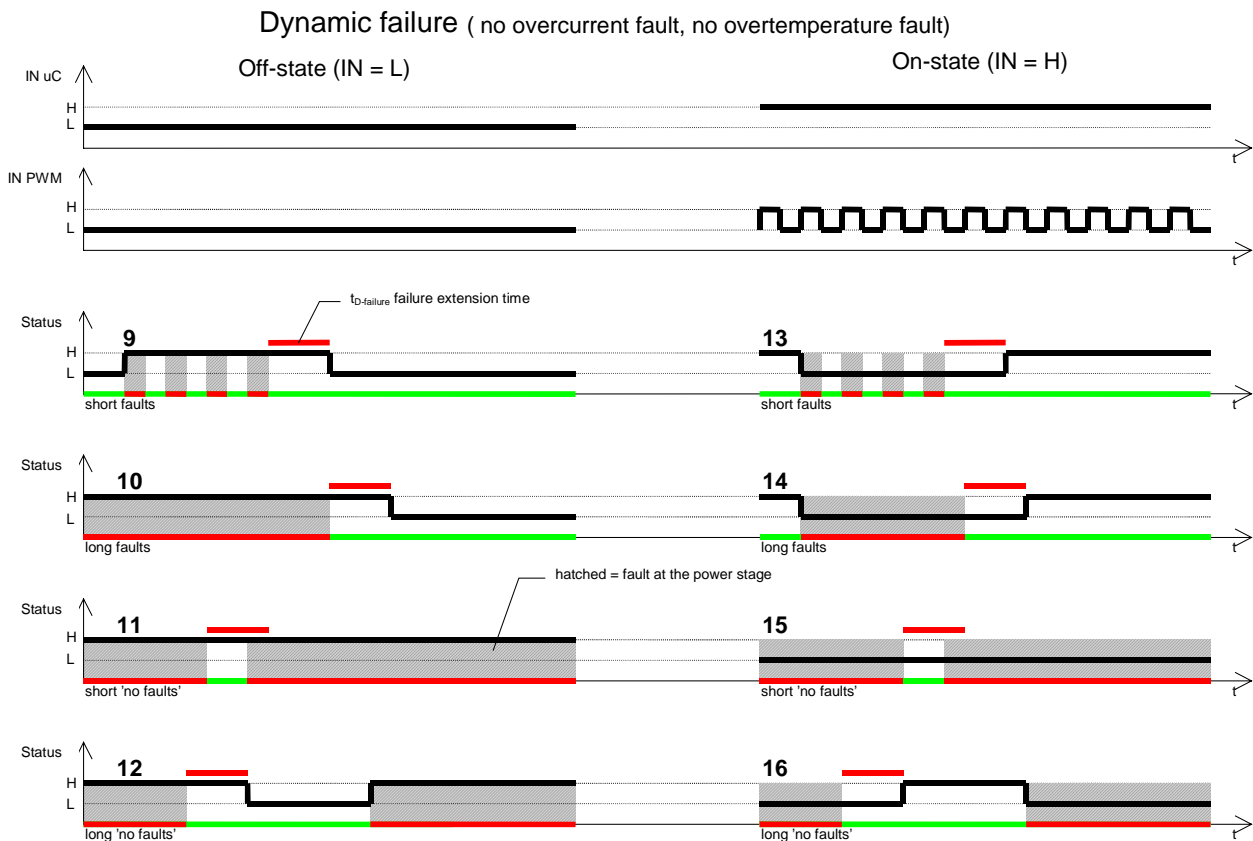
t_D is the output off status delay time. This delay provides a steady status signal during PWM control (number 5).

$t_{D-failure}$ extends the failure status report (number 6 and 8).

t_{D-IN} is the input suppression time to suppress input signals for example after a overload condition (number 19).

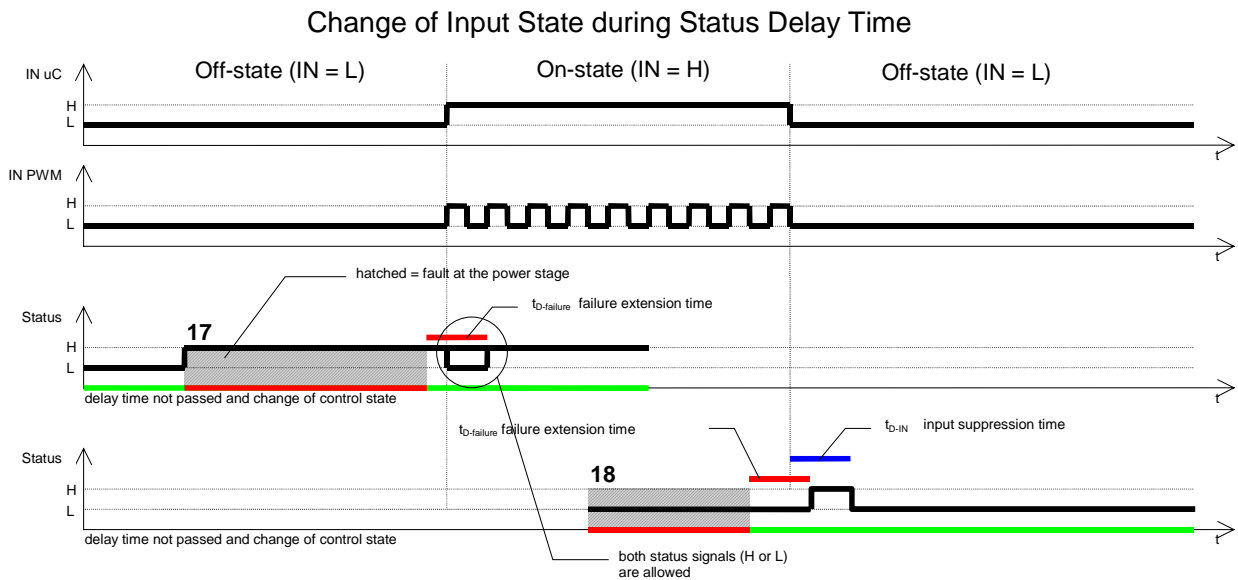
2. Dynamic failure (no overload faults, no overtemperature faults)

Nr.	Off-state	Nr.	On-state
9	short term faults	13	short term faults
10	long term faults	14	long term faults
11	short term 'no faults'	15	short term 'no faults'
12	long term 'no faults'	16	long term 'no faults'



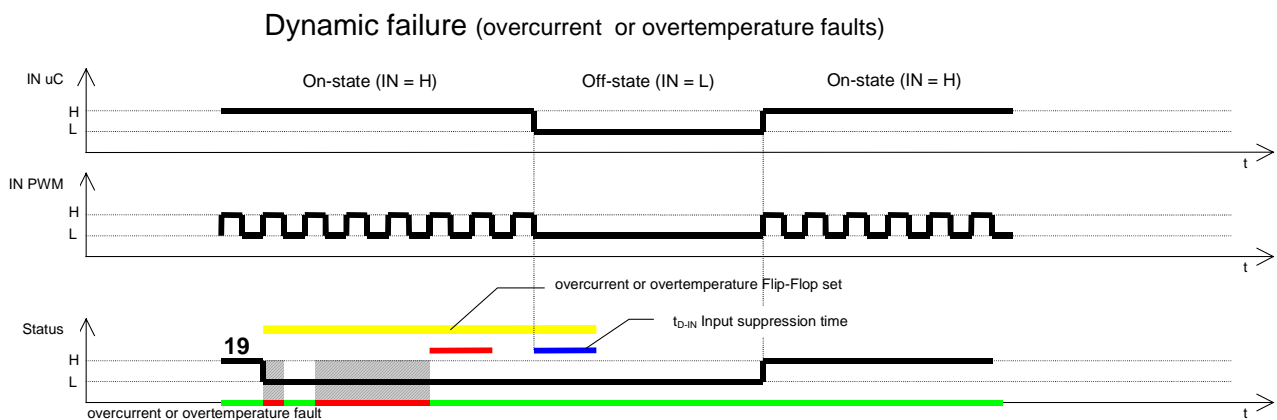
3. Change of input state during fault delay time

Nr.	Change from
17	Off-state (IN = L) to On-state (IN = H)
18	On-state (IN = H) to Off-state (IN = L)



4. Dynamic failure (Overload or overtemperature faults)

Nr.	On-state (IN = H)
19	Overload or overtemperature faults



Note: The diagrams before do not show the 'output on status delay time' t_{dST} and the 'overload switch off delay time' t_{dSO} . See timing diagram on page 12.

Timing Diagrams

Output Slope

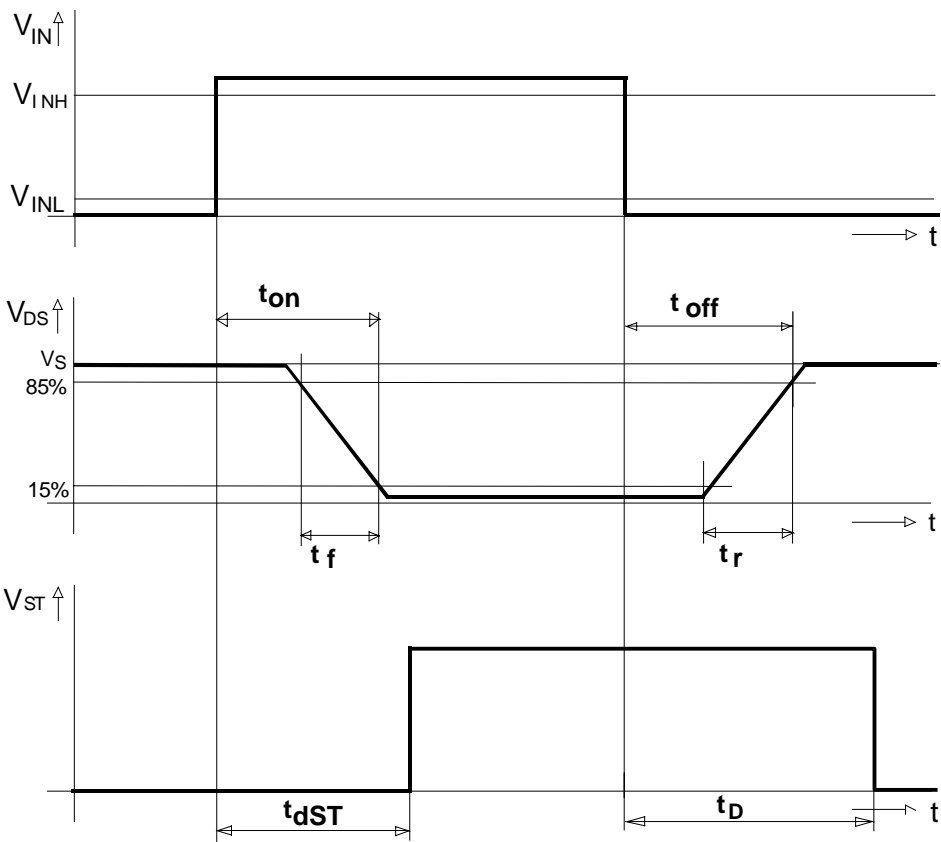


Fig. 1

Overload Switch OFF Delay

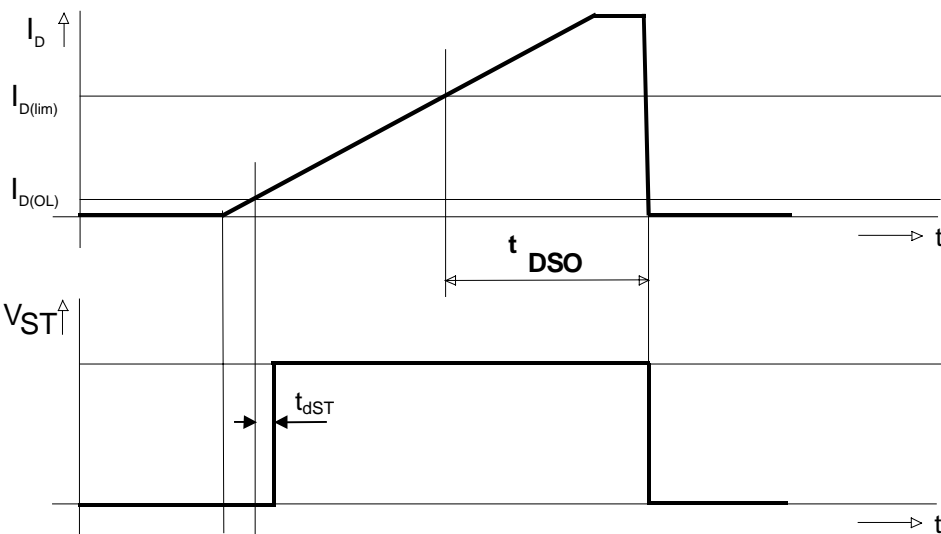
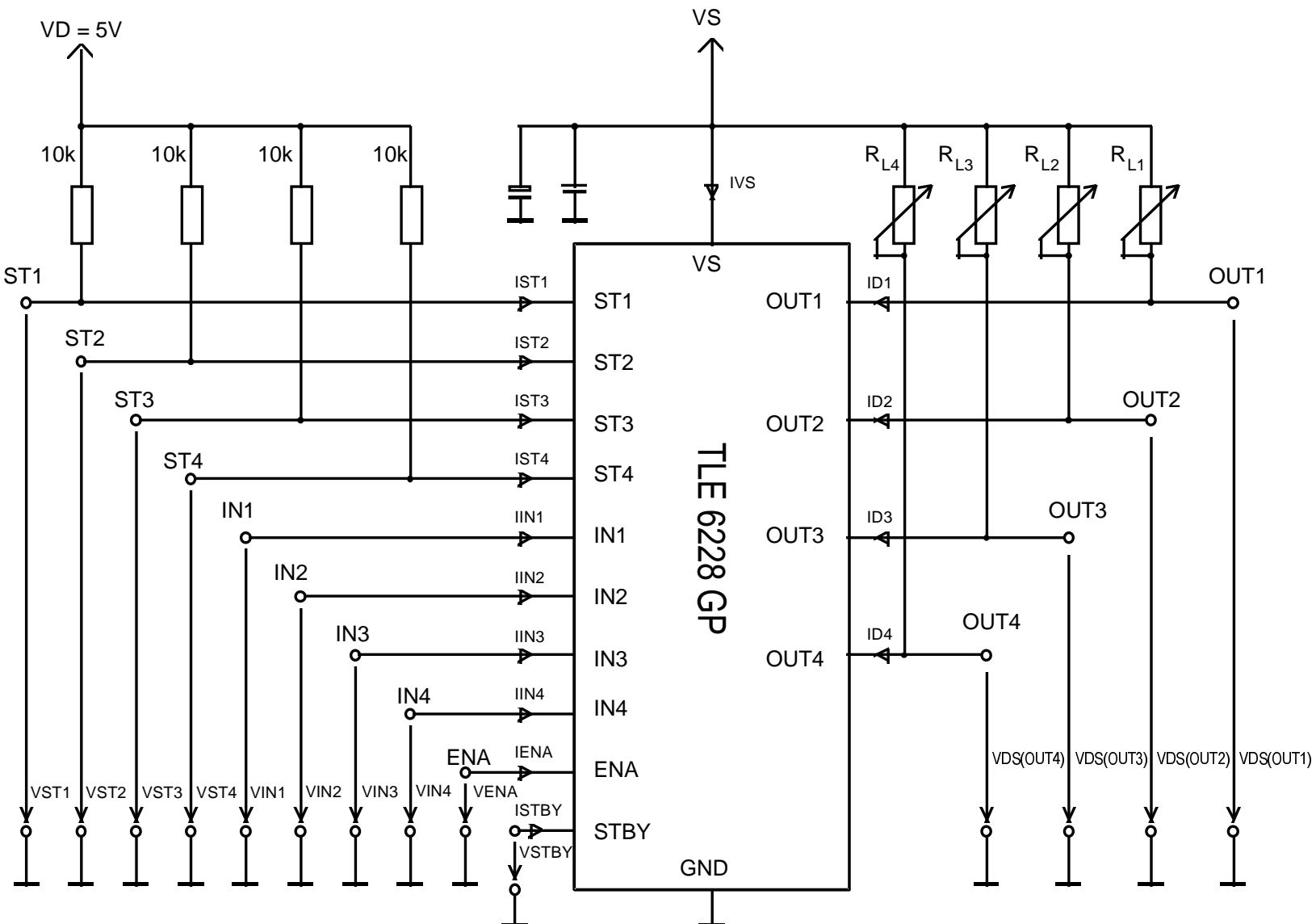
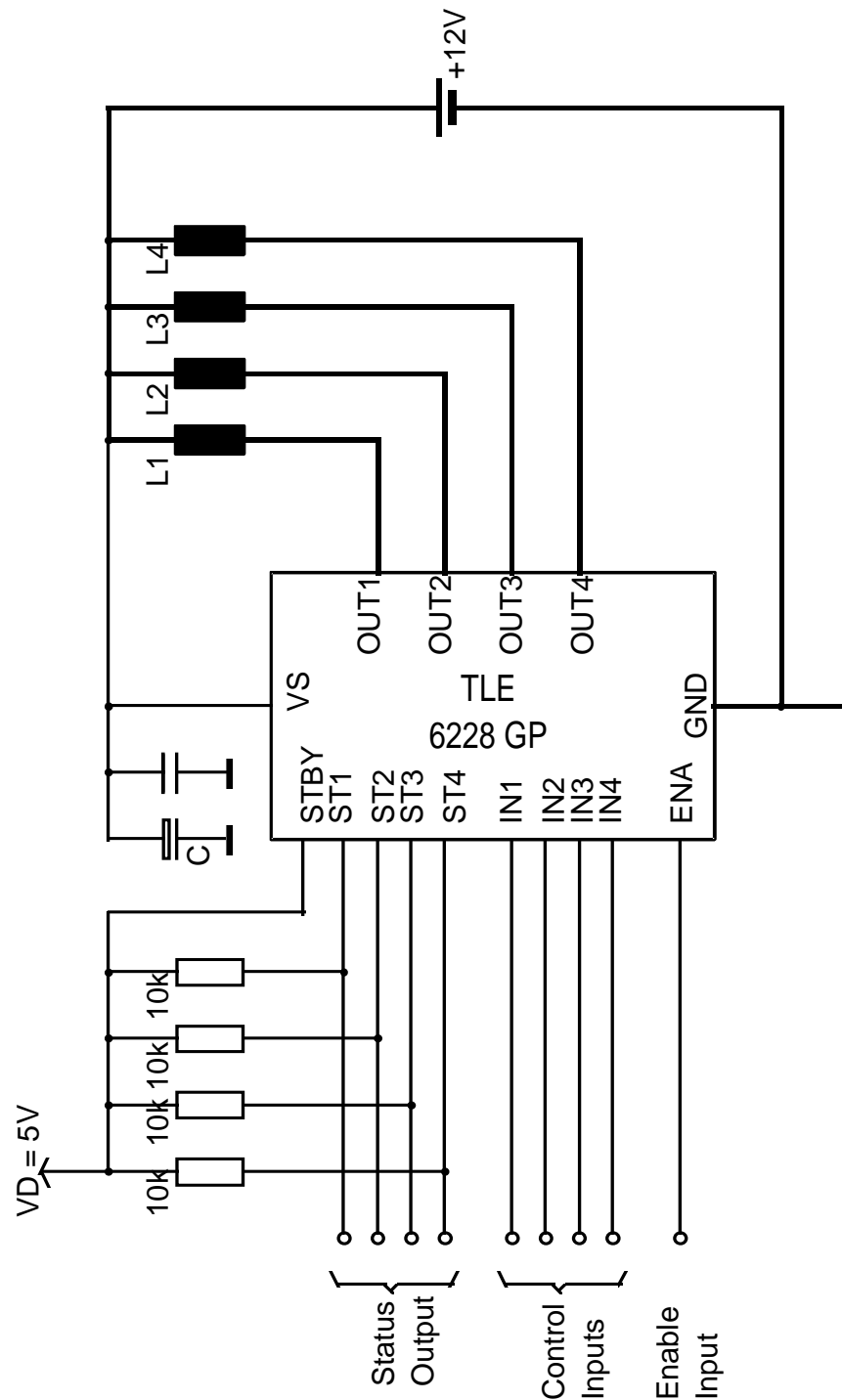


Fig. 2

Test Circuit



Application Circuit



The blocking capacitor C is recommended to avoid critical negative voltage spikes on VS in case of battery interruption during OFF-commutation.

Timing Diagrams of Diagnostic with Pulsed Input Signal

Normal condition, resistive load, pulsed input signal

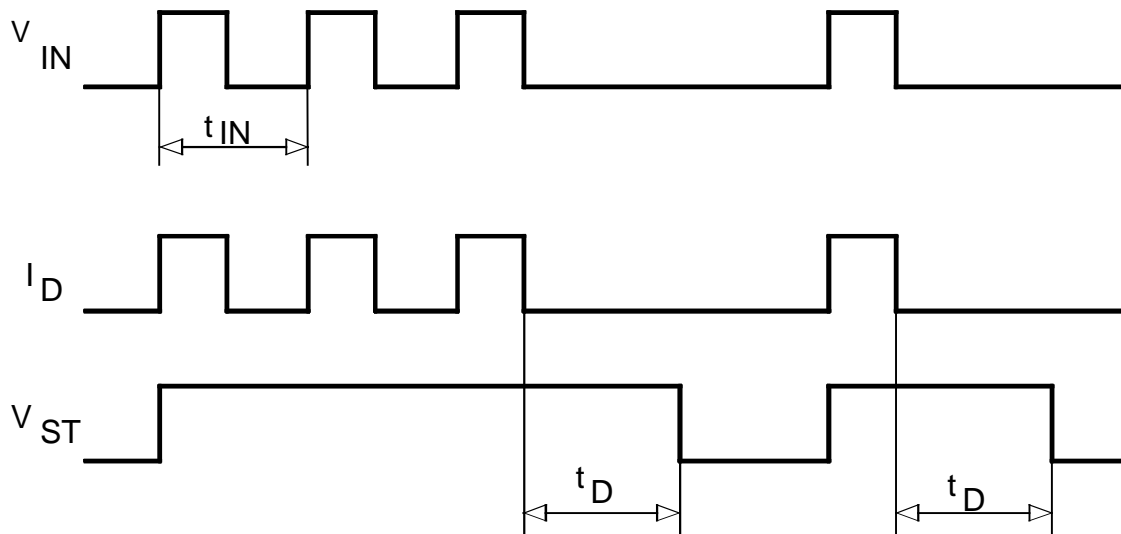
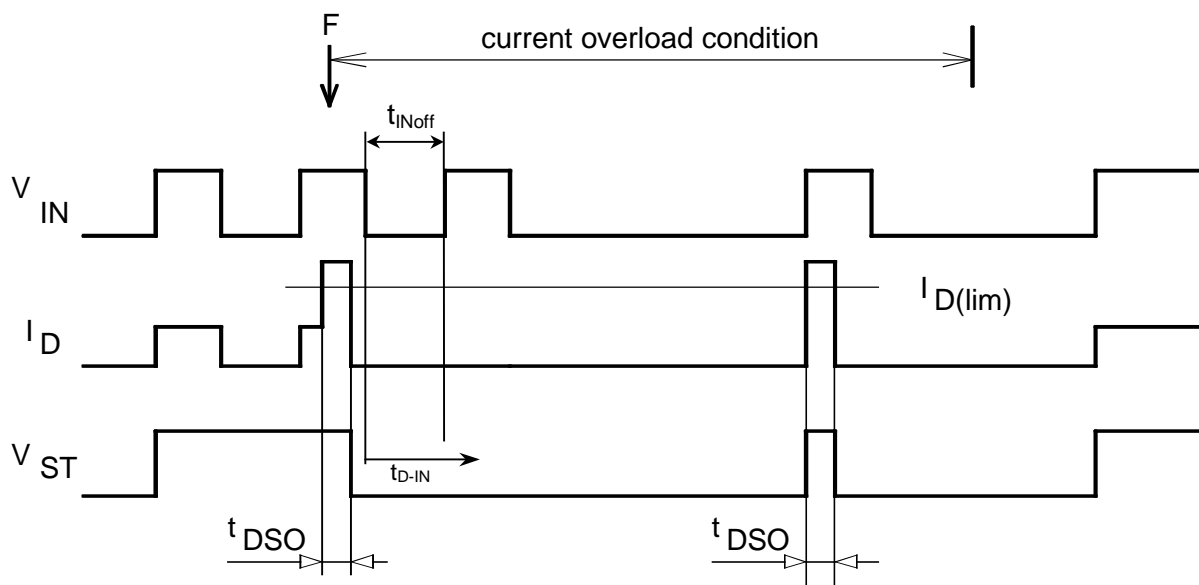


Fig. 3

Current Overload



$t_{INoff} < t_{D-IN}$: Input suppression time avoids a restart after overtemperature

Fig. 4

Diagnostic status output at different open load current conditions

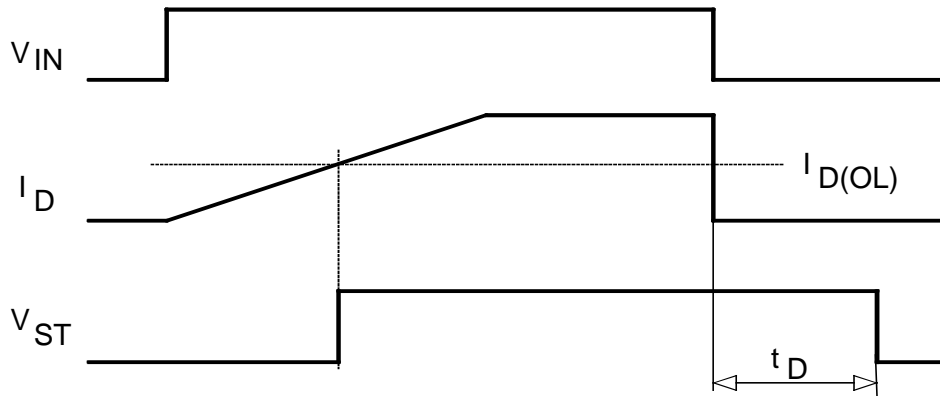
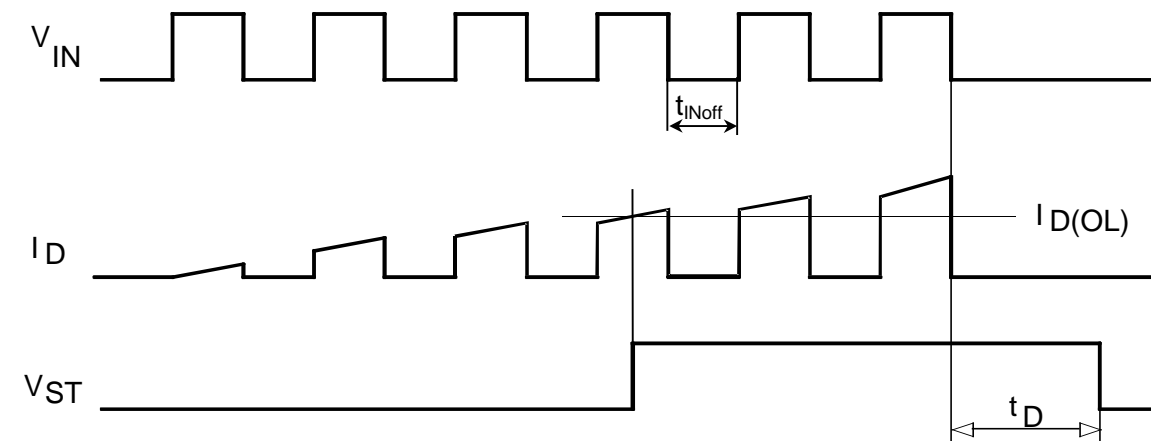
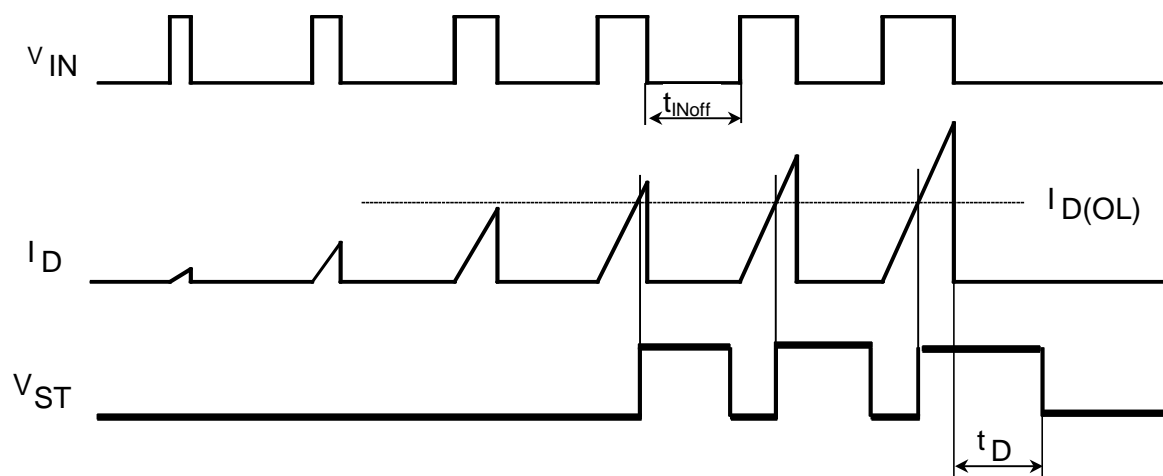


Fig. 5



$t_{INOFF} < t_D$ leads to a static status signal

Fig. 6



$t_{INoff} > t_D$: Intermittend status signal

Fig. 7

Normal operation, followed by open load condition

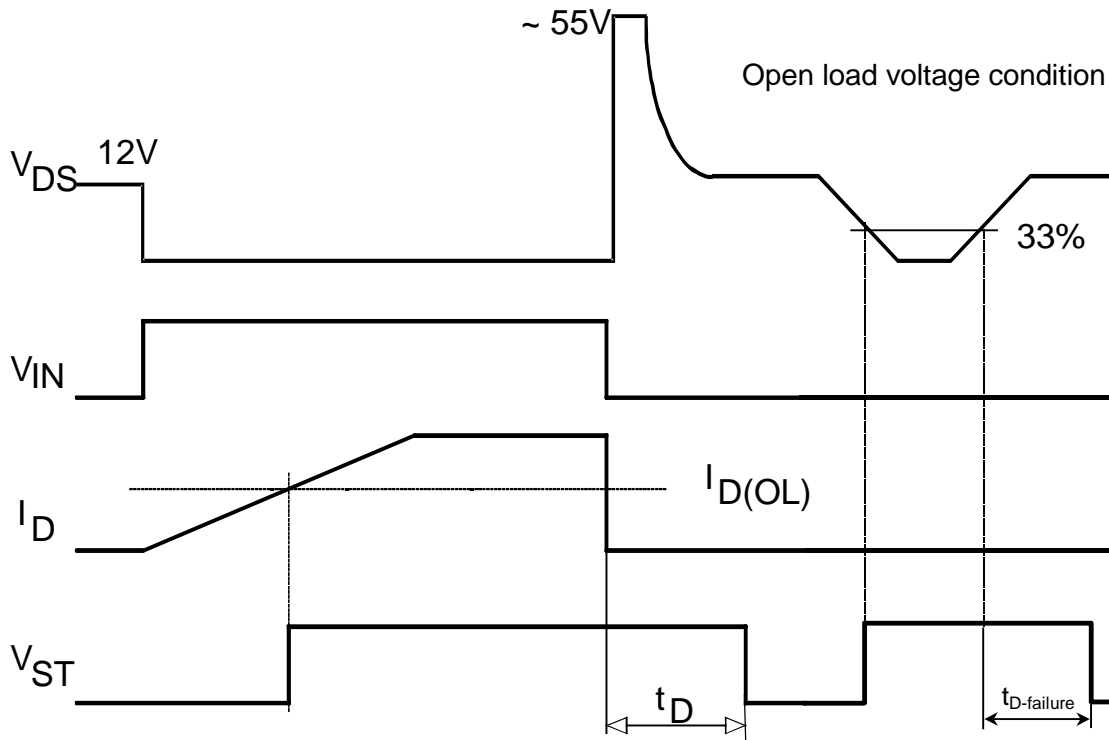


Fig. 8

Overtemperature

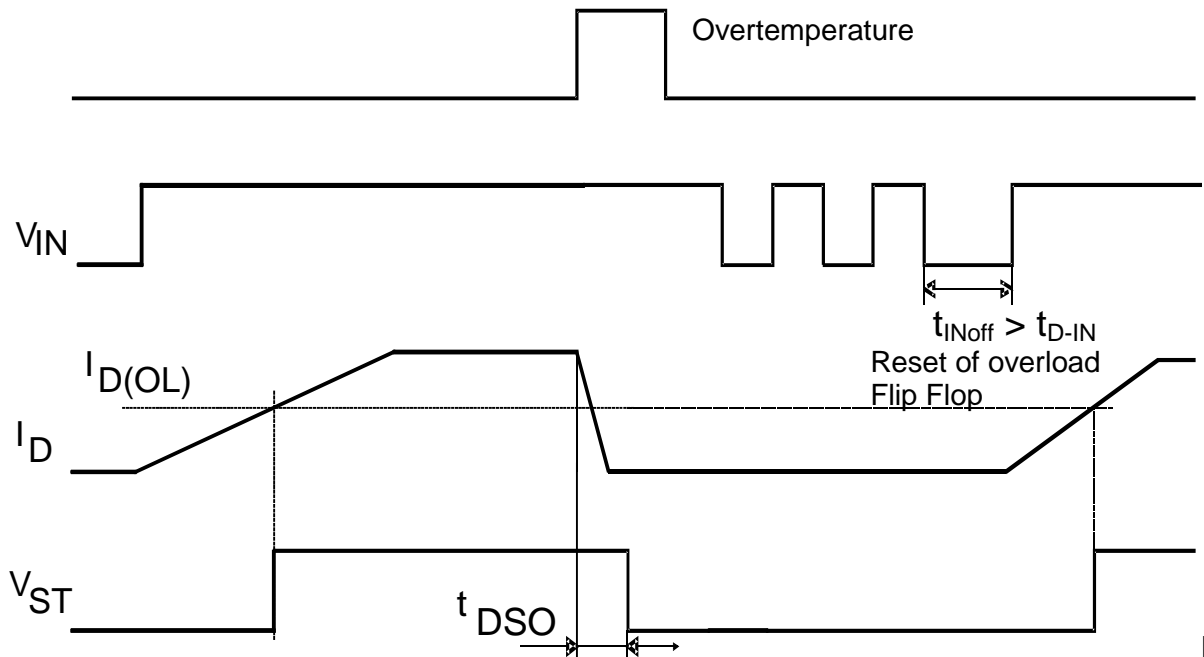


Fig. 9

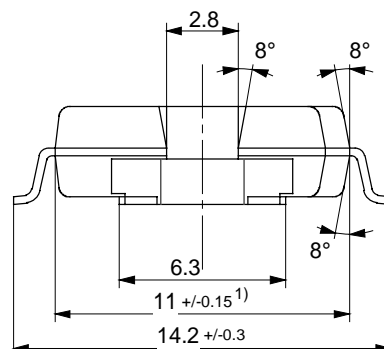
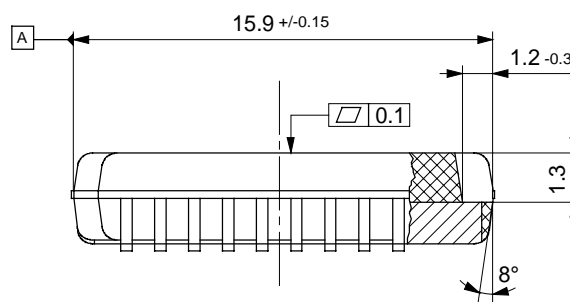
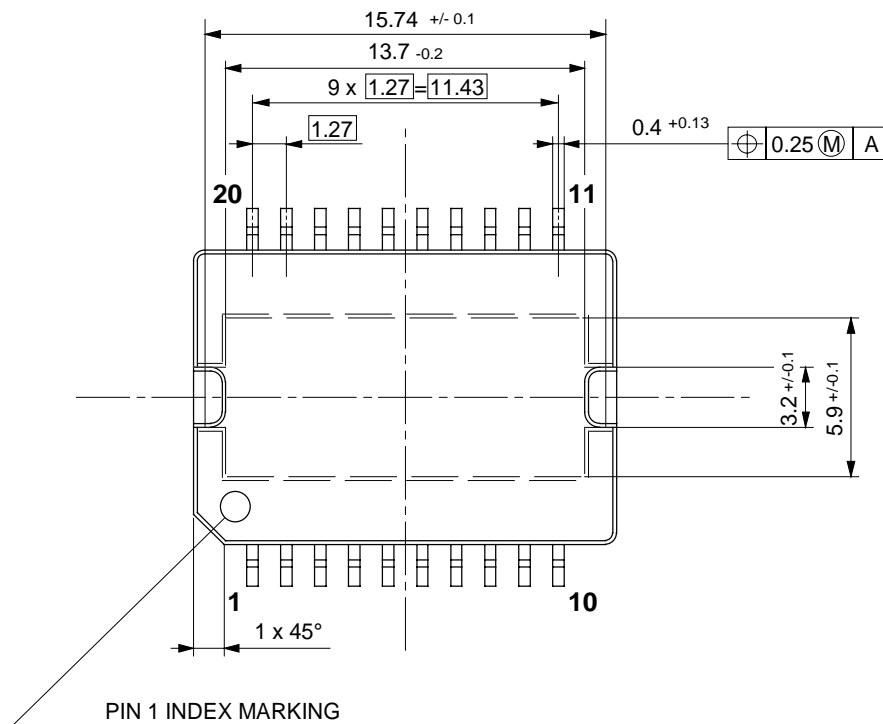
Package and ordering code

all dimensions in mm

P - DSO - 20 - 10

Ordering code

TLE 6228 GP	Q -A
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Published by Siemens AG,
Bereich Halbleiter Vertrieb,
Werbung, Balanstraße 73,
81541 München

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